

2SA1123

Silicon PNP epitaxial planar type

For low-frequency high breakdown voltage amplification
Complementary to 2SC2631

■ Features

- Satisfactory forward current transfer ratio h_{FE} collector current I_C characteristics.
- High collector-emitter voltage (Base open) V_{CEO}
- Small collector output capacitance (Common base, input open circuited) C_{ob}
- Makes up a complementary pair with 2SC2631, which is optimum for the pre-driver stage of a 20 W to 40 W output amplifier.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-150	V
Collector-emitter voltage (Base open)	V_{CEO}	-150	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-50	mA
Peak collector current	I_{CP}	-100	mA
Collector power dissipation	P_C	750	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

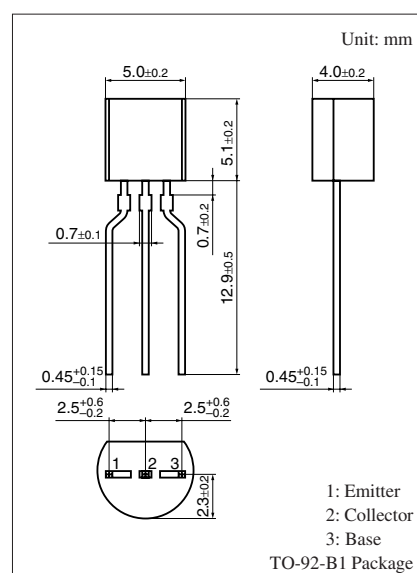
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

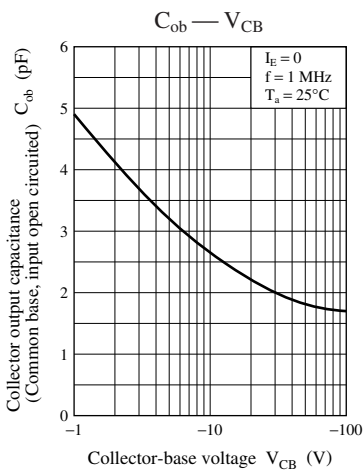
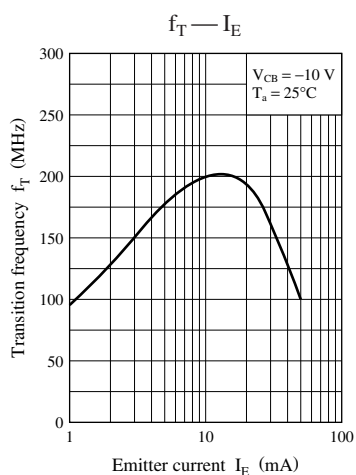
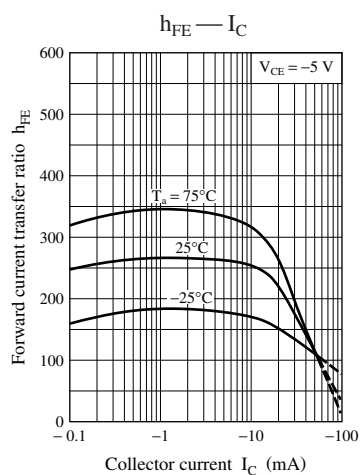
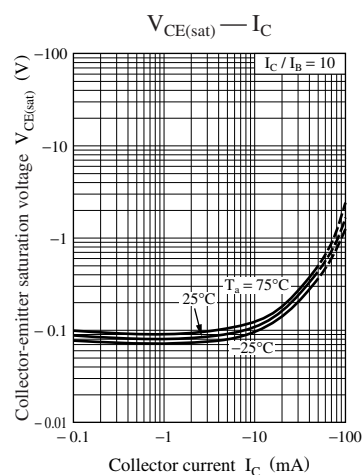
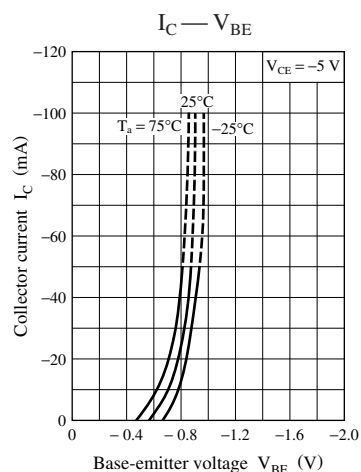
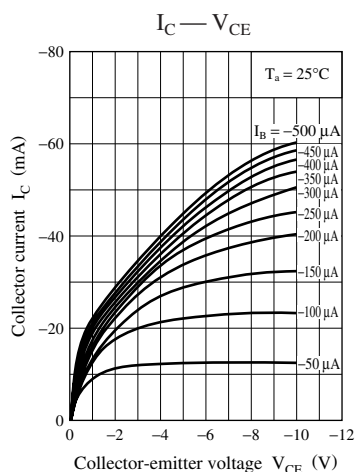
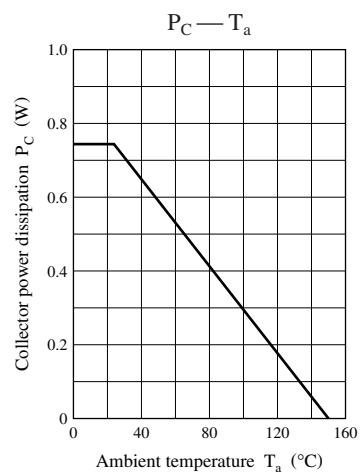
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -100\ \mu\text{A}$, $I_B = 0$	-150			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10\ \mu\text{A}$, $I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -100\ \text{V}$, $I_E = 0$			-1	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = -5\ \text{V}$, $I_C = -10\ \text{mA}$	130		450	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -30\ \text{mA}$, $I_B = -3\ \text{mA}$			-1	V
Transition frequency	f_T	$V_{CB} = -10\ \text{V}$, $I_E = 10\ \text{mA}$, $f = 200\ \text{MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$			5	pF
Noise voltage	NV	$V_{CE} = -40\ \text{V}$, $I_C = -1\ \text{mA}$, $G_V = 80\ \text{dB}$ $R_g = 100\ \text{k}\Omega$, Function = FLAT		150	300	mV

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	S	T
h_{FE}	130 to 220	185 to 330	260 to 450





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